

Atty. Docket No. OPP031050US
Serial No: 10/722,299

Amendments to the Claims

Please amend claims 1, 3-10 and 12-17, and add new claims 18-20, as follows:

1. (Currently Amended) A method for fabricating a metal line of a semiconductor device, comprising the steps of:
 - forming an insulation layer on a semiconductor substrate on which devices or lower lines are formed;
 - forming a metal layer on the insulation layer;
 - forming a photoresist pattern having an opening of certain width on the metal layer;
 - forming a buffer layer on the photoresist pattern, including in the opening; and
 - selectively removing the metal layer at a lower side of the opening by performing a dry etching process to form a plurality of metal lines such that a dimension between adjacent metal lines is less than said certain width of said opening.
2. (Original) The method of claim 1, further comprising a step of forming an organic anti-reflection coating between the metal layer and the photoresist pattern.
3. (Currently Amended) The method of claim 2, wherein the buffer layer ~~is made of~~ comprises an oxide film of PE family.
4. (Currently Amended) The method of claim 3, wherein the buffer layer ~~is formed~~ at has a thickness of 180 to 230Å.
5. (Currently Amended) The method of claim 4, wherein the metal layer comprises ~~three layers of~~ a lower metal layer, an intermediate metal layer and an upper metal layer.
6. (Currently Amended) The method of claim 5, wherein the lower metal layer is ~~made of~~ comprises TiN/Ti.

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7. (Currently Amended) The method of claim 6, wherein the lower metal layer functions as a capping barrier layer.

8. (Currently Amended) The method of claim 5, wherein the intermediate metal layer ~~is made of~~ comprises Al-Cu alloy.

9. (Currently Amended) The method of claim 5, wherein the upper metal layer is ~~made of~~ comprises TiN/Ti.

10. (Currently Amended) The method of claim 9, wherein the upper metal layer functions as a barrier capping layer.

11. (Original) The method of claim 3, wherein the dry etching process is performed by a plasma etching using Cl_2/BCl_3 gases.

12. (Currently Amended) The method of claim 11, wherein the metal layer comprises three layers of a lower metal layer, an intermediate metal layer and an upper metal layer.

13. (Currently Amended) The method of claim 12, wherein the lower metal layer is ~~made of~~ comprises TiN/Ti.

14. (Currently Amended) The method of claim 13, wherein the lower metal layer functions as a capping barrier layer.

15. (Currently Amended) The method of claim 12, wherein the intermediate metal layer ~~is made of~~ comprises Al-Cu alloy.

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16. (Currently Amended) The method of claim 12, wherein the upper metal layer is ~~made of~~ comprises TiN/Ti.

17. (Currently Amended) The method of claim 16, wherein the upper metal layer functions as a ~~barrier~~ capping layer.

18. (New) The method of claim 1, wherein said dimension between said adjacent metal lines is less than said certain width of said opening by two times a thickness of said buffer layer at a sidewall of said opening.

19. (New) The method of claim 1, wherein said photoresist has a thickness of less than 9000 Å.

20. (New) The method of claim 1, wherein a ratio of said photoresist thickness to said certain width of said opening is less than about 3.5.